



IPW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Edward Y. CHANG Confirmation No: 4041
Appl. No. : 10/699,839
Filed : November 4, 2003
Title : GROWTH OF GaAs EPITAXIAL LAYERS ON Si SUBSTRATE
BY USING A NOVEL GeSi BUFFER LAYER

TC/A.U. : 2818
Examiner : M. C. Tran

Docket No.: : CHAN3228/REF
Customer No: : 23364

AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

This is in response to the Official Action of June 20, 2005, in connection with the above-identified application. This response is timely filed.

Please amend the application as follows:

Amendments to the claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks begin on page 5 of this paper.